Sheet 1 of 1 Atty. Docket No. Serial No. 340-80 Applicant 10/686,520 **INFORMATION DISCLOSURE CITATION** MAY 2 5 2005 KOCHERGIN et al. (Use several sheets if necessary) TC/A.U. 16 October 2003 2872

EXAMINER			U.S. PATENT DOCUMENTS		01100:	FILING	DATE
INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	IF APPR	OPRIAT
		ļ					
	ļ	ļ		 		<u> </u>	
	ļ						
		ļ				ļ	
		ļ			ļ	<u> </u>	
						<u> </u>	
						ļ	
				 		ļ <u>.</u>	
	 	 		 	ļ		
				-		<u> </u>	
	 	-	· · · · · · · · · · · · · · · · · · ·	ļ		· · · · · · · · · · · · · · · · · · ·	
	 / 	 		 			
	/	-		 	 		
-		<u> </u>		 		 	
/		 		-			
		F01	CEICAL DATENT DOCUMENTO	J	<u> </u>	L	
			REIGN PATENT DOCUMENTS			TDANS	LATION
	DOCUMENT	DATE	COUNTRY	CLASS	SUBCLASS	YES	NO
				ļ			L
				9			
					l		
	OTHER DOC	JMENTS (ii	ncluding Author, Title, Date, Pertinent	pages, e	(c.)		*******
TAL	H H. Föll et al., "Porous	s III-V comp	ound semiconductors: formation, properties	and comp	arison to silic	con", Phy	vs. Stat.
CV.	Sol. A, 197 (1), pp. 61-7	0 (2003)		•			
4	S. Langa et al., Phys. St.	at. Sol. (A),	195 (3), "Electrochemical pore etching in Ge	," R4–R6 (2003)		
#	Macleod H.A., Thin-Fil	m Optical Fi	lters, 3rd ed., Institute of Physics Publishing	, 2001			
			P. D. W. C.				
							
							
					·		
				<u>_</u>	·		

*Examiner	de -	Date Considered	8/1	106

Examiner: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to application.